

Polar™ HiPerFET Power MOSFET

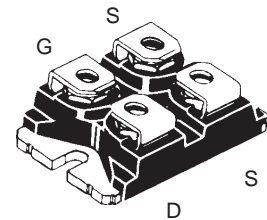
IXFN 200N10P

N-Channel Enhancement Mode
Fast Intrinsic Diode
Avalanche Rated



$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 200 \text{ A} \\ R_{DS(on)} &\leq 7.5 \text{ m}\Omega \\ t_{rr} &\leq 150 \text{ ns} \end{aligned}$$

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	200	A
$I_{D(RMS)}$	External lead current limit	100	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	400	A
I_{AR}	$T_C = 25^\circ\text{C}$	60	A
E_{AR}	$T_C = 25^\circ\text{C}$	100	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	4	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	680	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, $T = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$, $T = 1 \text{ s}$	2500 3000	V~ V~
M_d	Mounting torque, Terminal connection torque	1.5/13	lb.in.
Weight		30	g

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

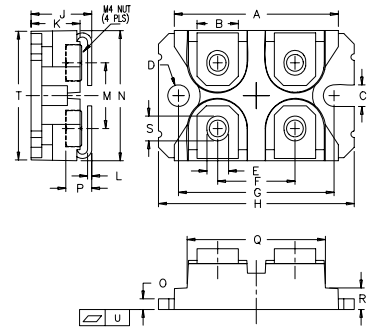
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$ $T_J = 175^\circ\text{C}$			25 μA 500 μA 2.5 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ $V_{GS} = 15 \text{ V}$, $I_D = 400 \text{ A}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$	5.5		7.5 m Ω m Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test	60	97	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		7600	pF
			2900	pF
			860	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 60\text{ A}$ $R_G = 3.3\ \Omega$ (External)		30	ns
			35	ns
			150	ns
			90	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$		235	nC
			50	nC
			135	nC
R_{thJC} R_{thCS}			0.22	$^\circ\text{C/W}$
		0.05		$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			200 A
I_{SM}	Repetitive			400 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr} Q_{RM} I_{RM}	$I_F = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 50\text{ V}$, $V_{GS} = 0\text{ V}$			150 ns
			0.4	μC
			6	A

SOT-227B (IXFN) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

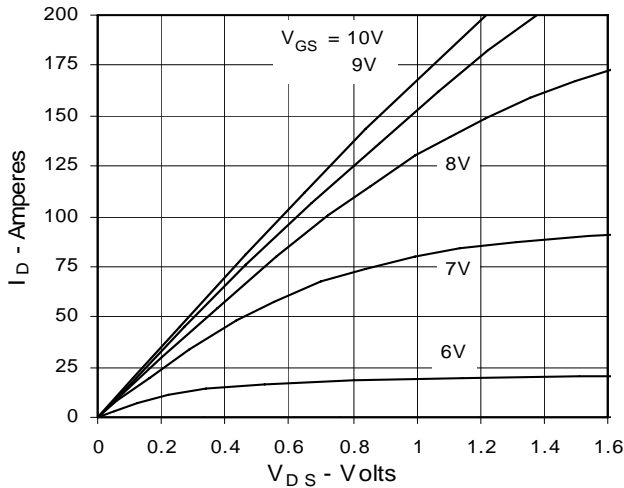
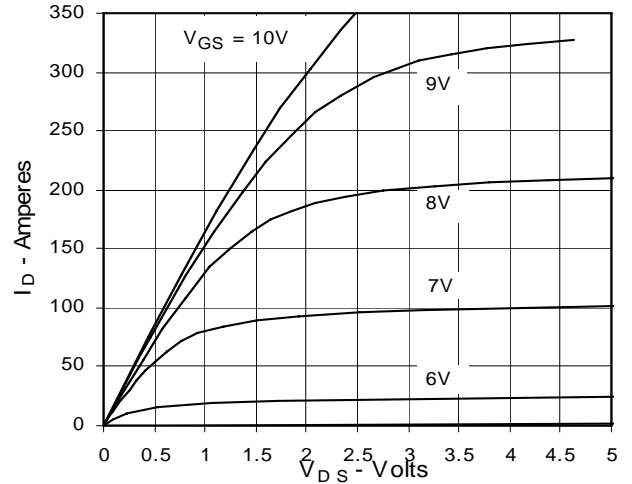
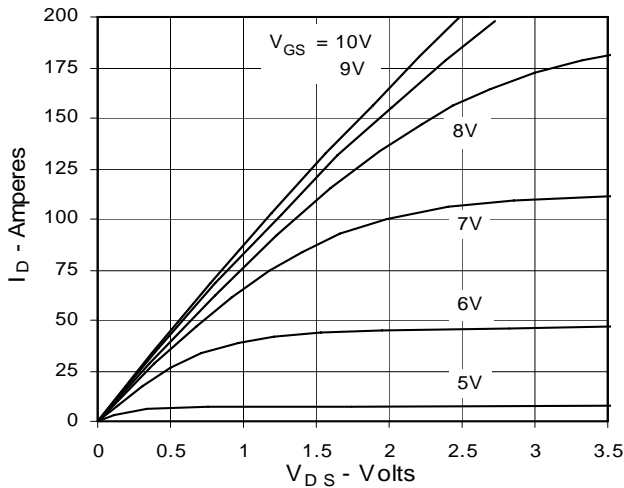
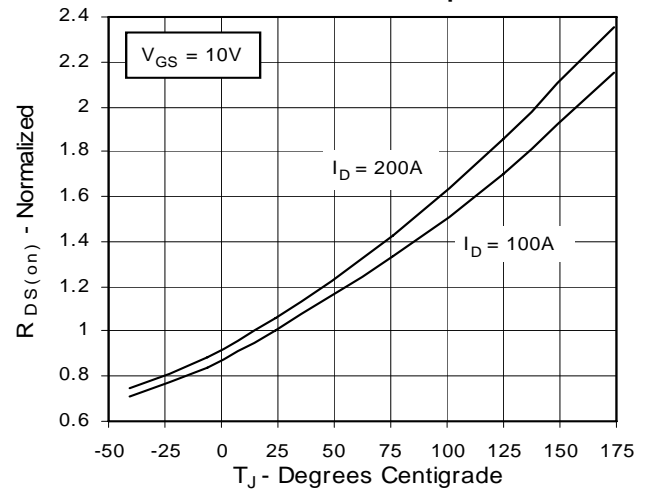
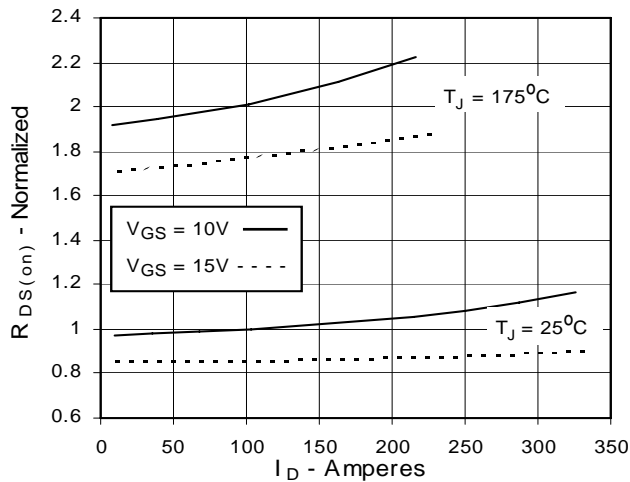
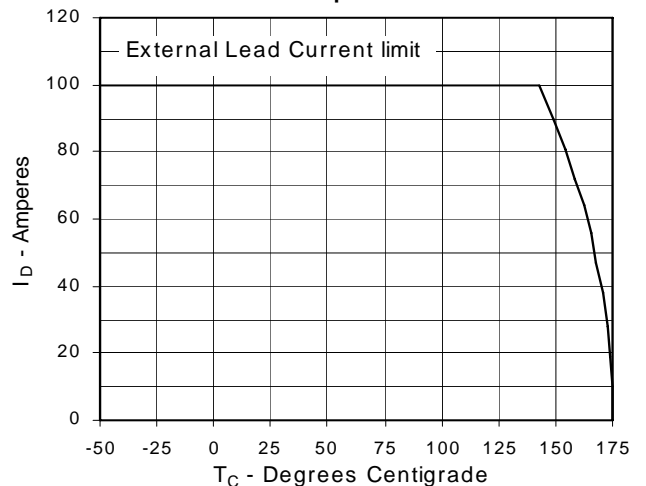
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 150°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100A$
Value vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100A$
Value vs. Drain Current**

**Fig. 6. Drain Current vs. Case
Temperature**


Fig. 7. Input Admittance

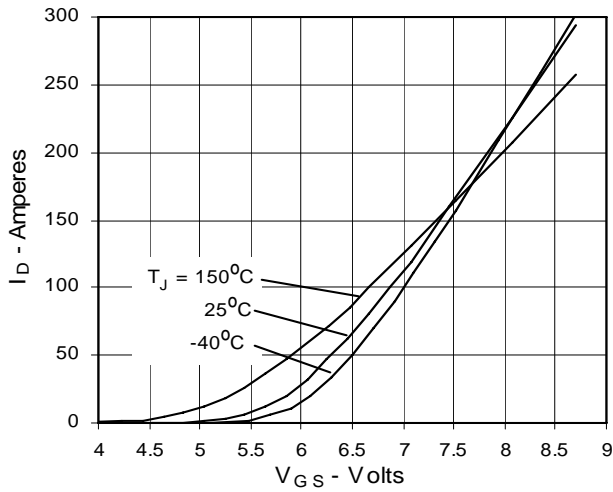


Fig. 8. Transconductance

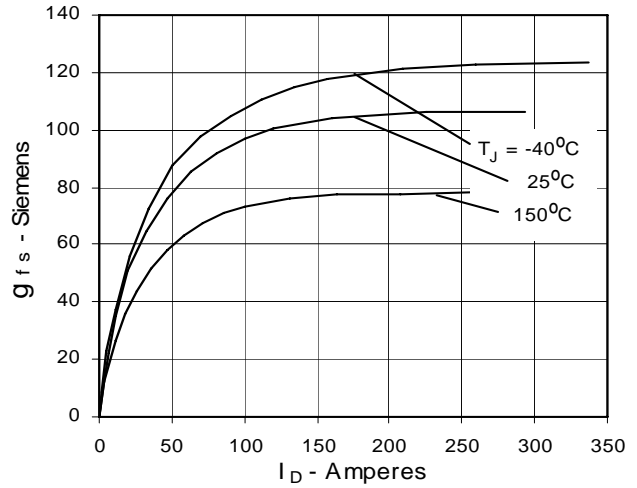


Fig. 9. Source Current vs. Source-To-Drain Voltage

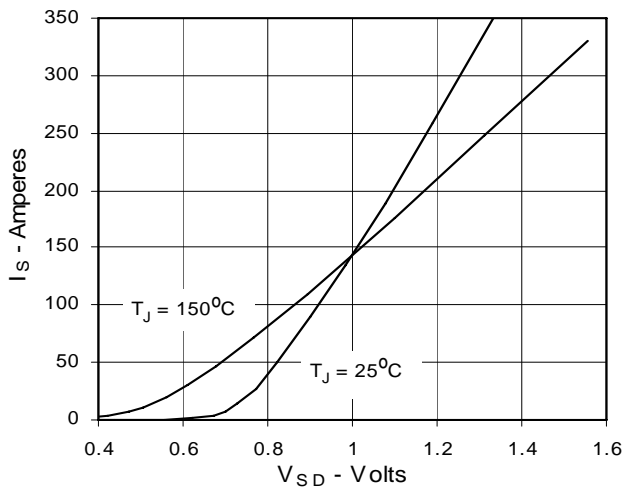


Fig. 10. Gate Charge

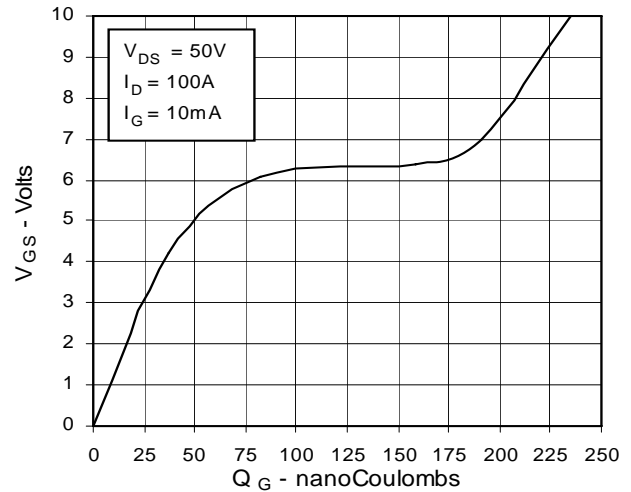


Fig. 11. Capacitance

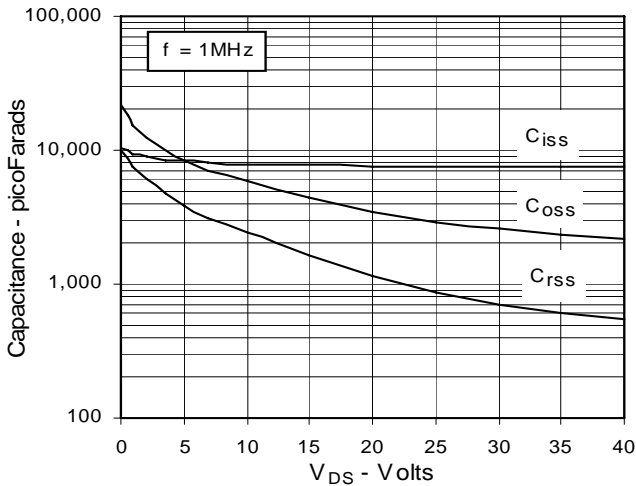


Fig. 12. Forward-Bias Safe Operating Area

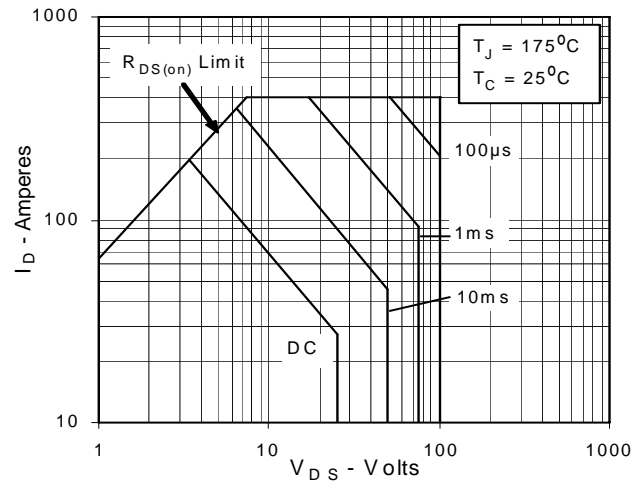


Fig. 13. Maximum Transient Thermal Resistance

